

RE-PERFORMABLE SPIN-ON PROCESS

Abstract

First, a spin-on process is performed for forming a first dielectric layer over a plurality of metal interconnecting wires that are located on a semiconductor wafer. Then, an examining step is performed on the first dielectric layer, and the first dielectric layer is made to conform to a predetermined condition. Thereafter, an etching process is performed for completely removing the first dielectric layer. Subsequently, the semiconductor wafer is cleaned through use of a wet scrubber, and is dried. Finally, the spin-on process is re-performed for forming a second dielectric layer on the semiconductor wafer.